

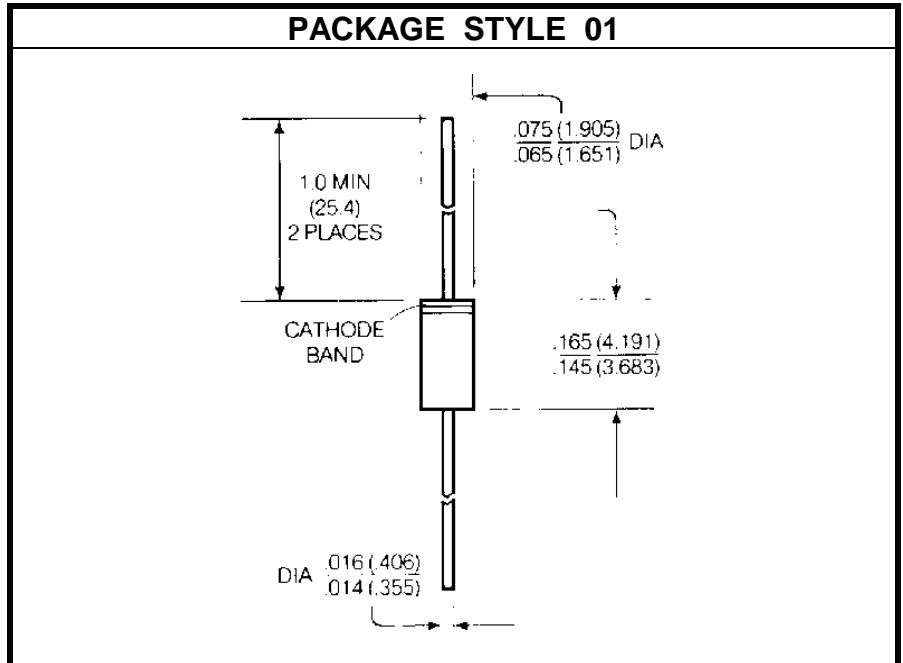
SILICON PIN DIODE CHIP

DESCRIPTION:

The **AP3000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of Control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

MAXIMUM RATINGS

I_F	100 mA
V_R	300 V
P_{DISS}	250 mW @ T _A = 25 °C
θ_{JC}	20 °C/W



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	I _R = 10 μA	300			V
C_J	V _R = 50 V V _R = 40 V		f = 1.0 MHz	0.2	pF
R_S	I _F = 50 mA		f = 100 MHz	0.6	Ohms
T_L	I _F = 10 mA I _R = 6.0 mA		1000		nS
T_{rr}	I _F = 20 mA I _R = 100 mA		100		nS